

1. Global joint venture starts operations as WeEn Semiconductors

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As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

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Thank you for your cooperation and understanding,

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Product data sheet

1. General description

Hyperfast power diode in a SOD59 (2-lead TO-220AC) plastic package.

2. Features and benefits

- Fast switching
- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET or IGBT

3. Applications

- Active PFC in air conditioner
- High frequency switched-mode power supplies
- Continuous Current Mode (CCM) Power Factor Correction (PFC)

4. Quick reference data

Table 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	-	600	V
I _{F(AV)}	average forward current	δ = 0.5; T _{mb} ≤ 120 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	-	20	A
Static character	eristics					
V _F	forward voltage	I _F = 20 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.2	1.97	V
Dynamic chara	acteristics					
t _{rr}	reverse recovery time	I_F = 1 A; V_R = 30 V; dI_F/dt = 200 A/µs; T _j = 25 °C; <u>Fig. 7</u>	-	16	20	ns





Hyperfast power diode

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	к	cathode	mb	K – A
2	А	anode	$1 \gamma \bigcirc 1$	001aaa020
mb	mb	mounting base; connected to cathode	C C C C C C C C C C C C C C C C C C C	

6. Ordering information

Table 3. Ordering in	formation					
Type number	Package					
	Name	Description	Version			
BYC20D-600P	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59			

7. Marking

Table 4. Marking codes	
Type number	Marking code
BYC20D-600P	BYC20D-600P

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	IV	Vin	Мах	Unit
V _{RRM}	repetitive peak reverse voltage		-	-	600	V
V _{RWM}	crest working reverse voltage		-	-	600	V
V _R	reverse voltage	DC	-	-	600	V
I _{F(AV)}	average forward current	δ = 0.5; T _{mb} ≤ 120 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	-	20	A
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _{mb} ≤ 120 °C; square-wave pulse	-	-	40	A
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Symbol	Parameter	Conditions	Min	Max	Unit
I _{FSM} non-repetitive peak forward current	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	250	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	275	А
T _{stg}	storage temperature		-65	175	°C
Tj	junction temperature		-	175	°C

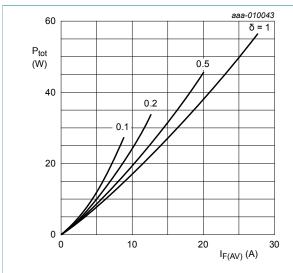


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$

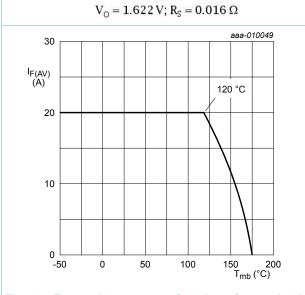


Fig. 3. Forward current as a function of mounting base Fig. 4. temperature; maximum values

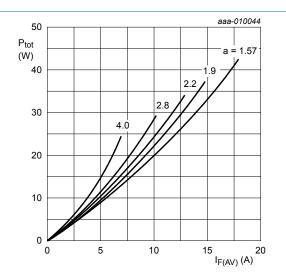
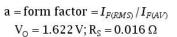
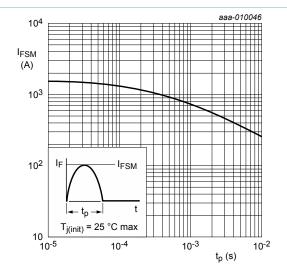


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values



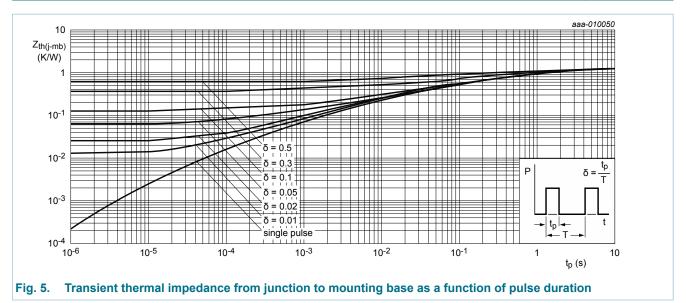


4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

Hyperfast power diode

9. Thermal characteristics

Table 6. Tl	hermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	with heatsink compound; Fig. 5	-	-	1.2	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W



10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · · · ·	,			
V _F forward voltage		I _F = 20 A; T _j = 25 °C; <u>Fig. 6</u>	-	2	2.9	V
		I _F = 20 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.2	1.97	V
I _R reve	reverse current	V _R = 600 V; T _j = 25 °C	-	-	10	μA
		V _R = 600 V; T _j = 150 °C	-	-	1	mA
Dynamic cl	naracteristics		I			
Q _r recove	recovered charge	$I_F = 20 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 25 \text{ °C}; Fig. 7$	-	47	-	nC
		I _F = 20 A; V _R = 200 V; dI _F /dt = 200 A/ μs; T _j = 125 °C; <u>Fig. 7</u>	-	193	-	nC

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{rr} reverse recovery time	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	16	20	ns
	I _F = 20 A; V _R = 400 V; dI _F /dt = 500 A/ μs; T _j = 25 °C; <u>Fig. 7</u>	-	26	-	ns	
		I _F = 20 A; V _R = 200 V; dI _F /dt = 200 A/ μs; T _j = 25 °C; <u>Fig. 7</u>	-	33	-	ns
		I _F = 20 A; V _R = 200 V; dI _F /dt = 200 A/ μs; T _j = 125 °C; <u>Fig. 7</u>	-	51	-	ns
I _{RM}	peak reverse recovery current	I _F = 20 A; V _R = 200 V; dI _F /dt = 200 A/ μs; T _j = 25 °C; <u>Fig. 7</u>	-	2.8	-	A
		I _F = 20 A; V _R = 200 V; dI _F /dt = 200 A/ μs; T _j = 125 °C; <u>Fig. 7</u>	-	7.6	-	A

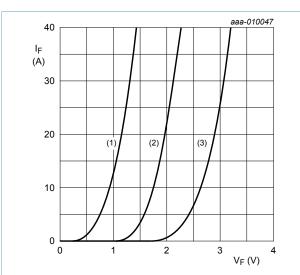


Fig. 6. Forward current as a function of forward voltage

(1) $T_j = 150$ °C; typical values; (2) $T_j = 150$ °C; maximum values; (3) $T_j = 25$ °C; maximum values; $V_0 = 1.622$ V; $R_s = 0.016 \Omega$

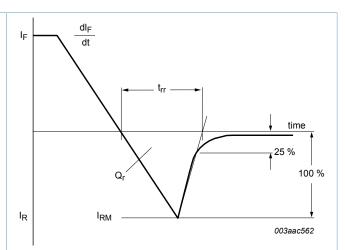
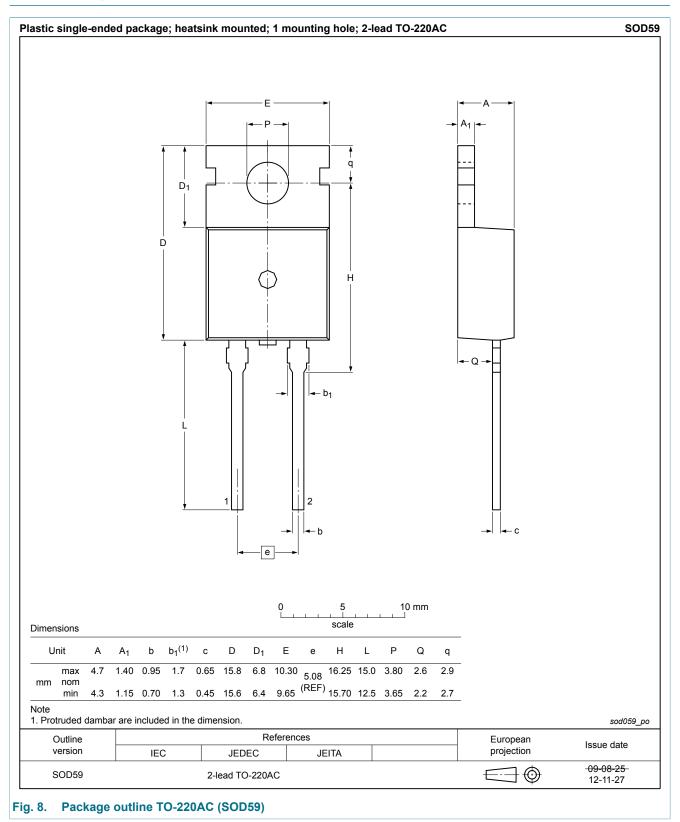


Fig. 7. Reverse recovery definitions; ramp recovery

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11. Package outline



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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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13. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	2
9	Thermal characteristics	4
10	Characteristics	4
11	Package outline	6
12	Legal information	7
12.1	Data sheet status	7
12.2	Definitions	7
12.3	Disclaimers	7
12.4	Trademarks	8

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